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TPC8107

P-Channel Enhancement Mode Power MOSFET

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GENERAL FEATURES

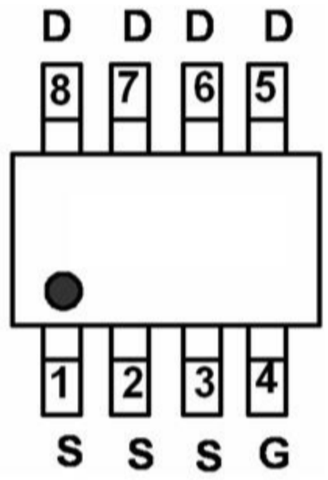
- V_{DS} = -30V I_D =-60 A
- $R_{DS(ON)}$ < 11 mΩ @ V_{GS}=10V

Application

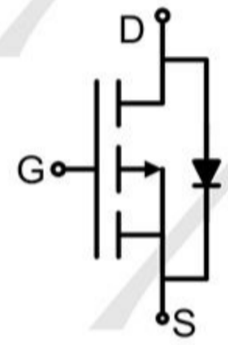
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

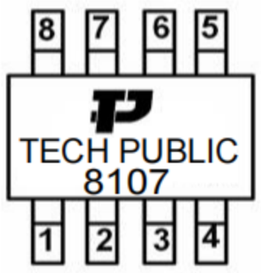
SOP-8 top view



Circuit diagram



Marking:



Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Rating		Units
		10s	Steady State	
VDS	Drain-Source Voltage	-30		V
VGS	Gate-Source Voltage	±20		V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-15		A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V[1]	-12		A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-14.3	-9	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-11.4	-7.2	A
IDM	Pulsed Drain Current[2]	-130		A
EAS	Single Pulse Avalanche Energy[3]	125		mJ
IAS	Avalanche Current	-50		A
P_D@T_C=25℃	Total Power Dissipation[4]	37		W
P_D@T_A=25℃	Total Power Dissipation[4]	4.2	1.67	W
TSTG	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Electrical Characteristics (T_A=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.0232	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-10A	---	---	11	mΩ
		V_{GS}=-4.5V , I_D=-8A	---	---	20	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	---	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-30A	---	30	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	9	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-15A	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	8.7	---	
Q_{gd}	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3 I_D=-15A	---	8	---	ns
T_r	Rise Time		---	73.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	61.8	---	
T_f	Fall Time		---	24.4	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	2215	---	pF
C_{oss}	Output Capacitance		---	310	---	
C_{rss}	Reverse Transfer Capacitance		---	237	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-42	A
I_{SM}	Pulsed Source Current[2,5]		---	---	-130	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V
t_{rr}	Reverse Recovery Time	I_F=-15A , dI/dt=100A/μs , T_J=25℃	---	19	---	nS
Q_{rr}	Reverse Recovery Charge		---	9	---	nC

Typical Electrical and Thermal Characteristics

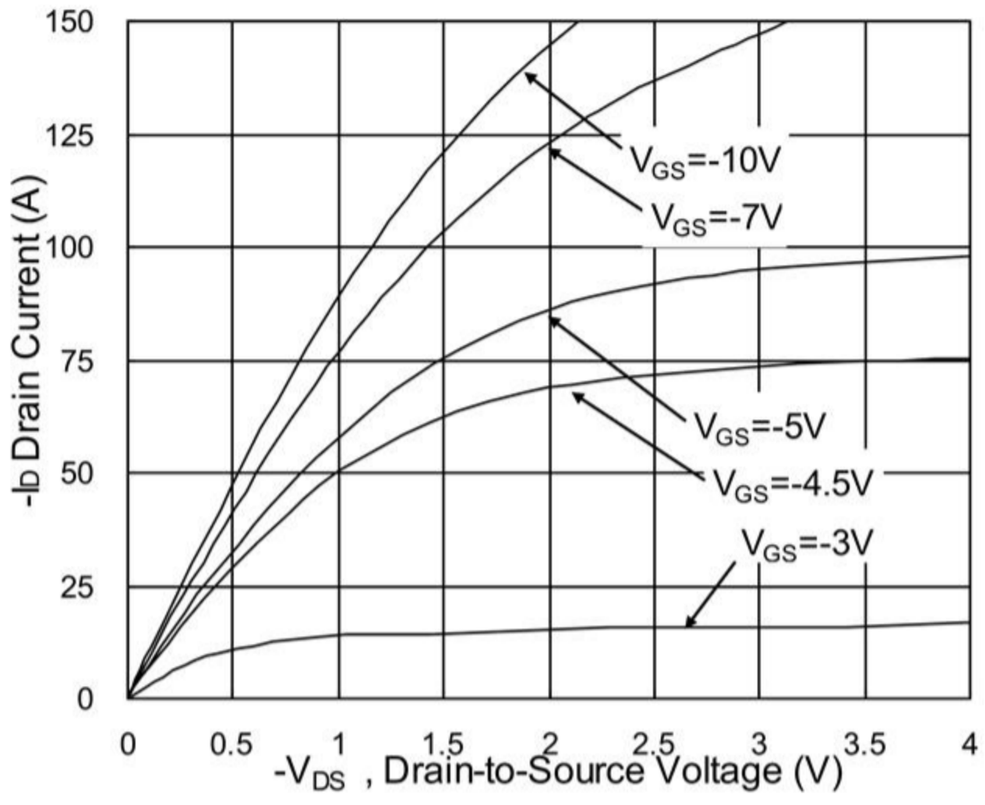


Fig.1 Typical Output Characteristics

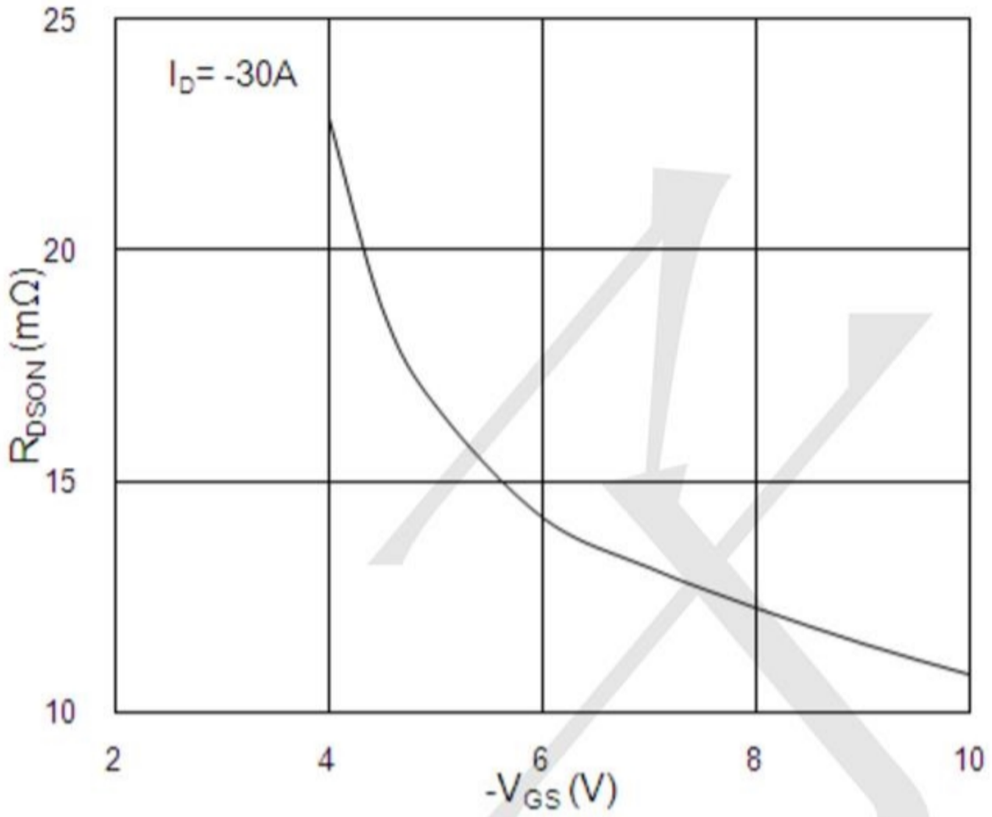


Fig.2 On-Resistance vs. G-S Voltage

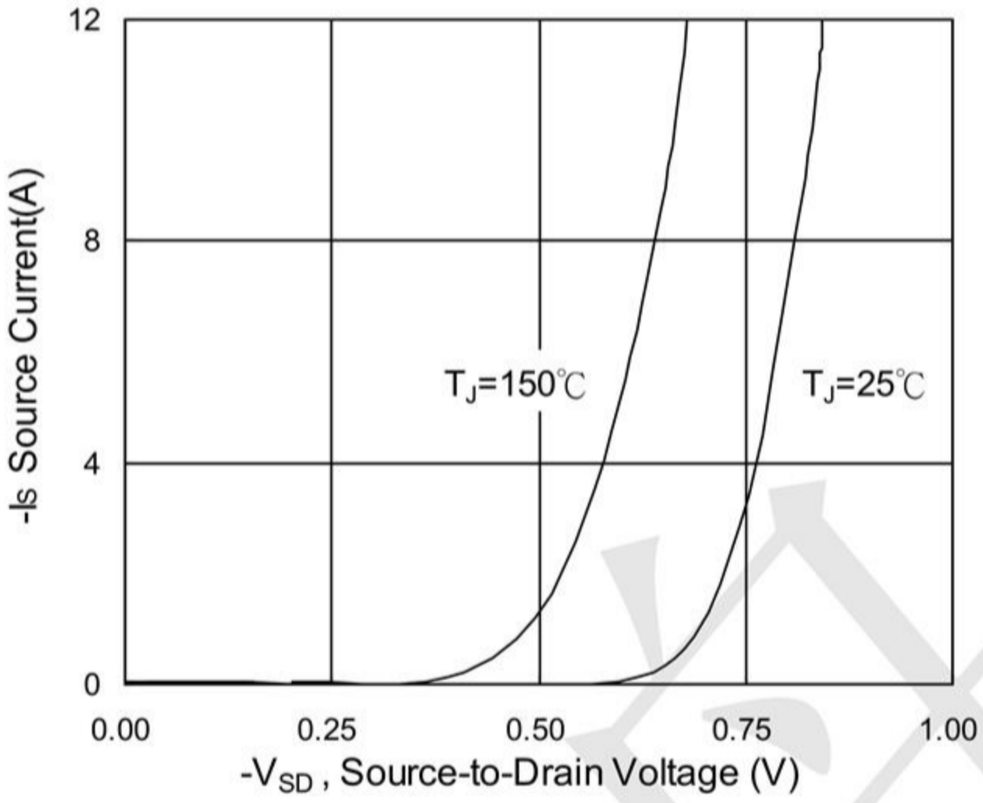


Fig.3 Forward Characteristics of Reverse

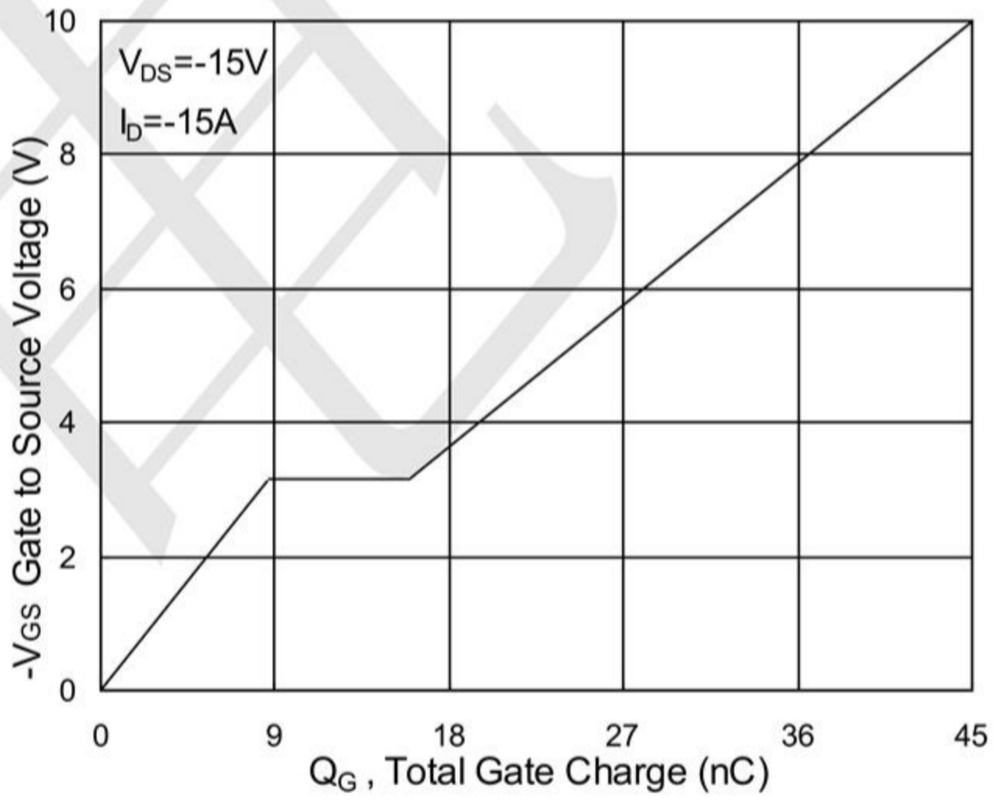


Fig.4 Gate-Charge Characteristics

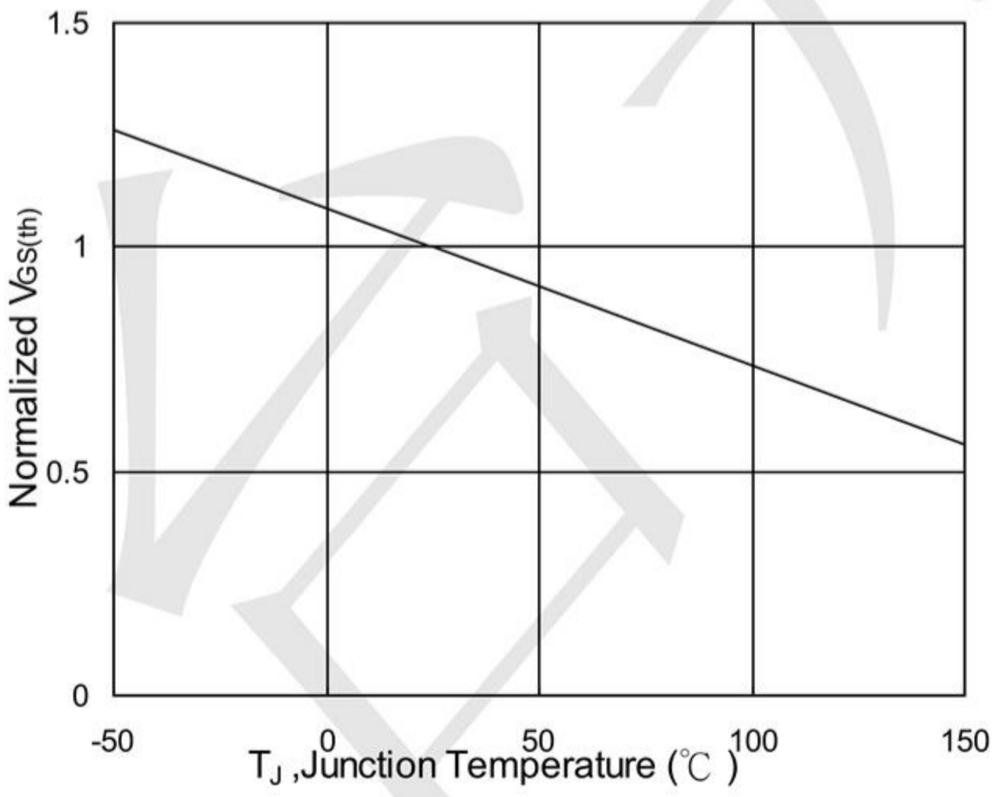


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

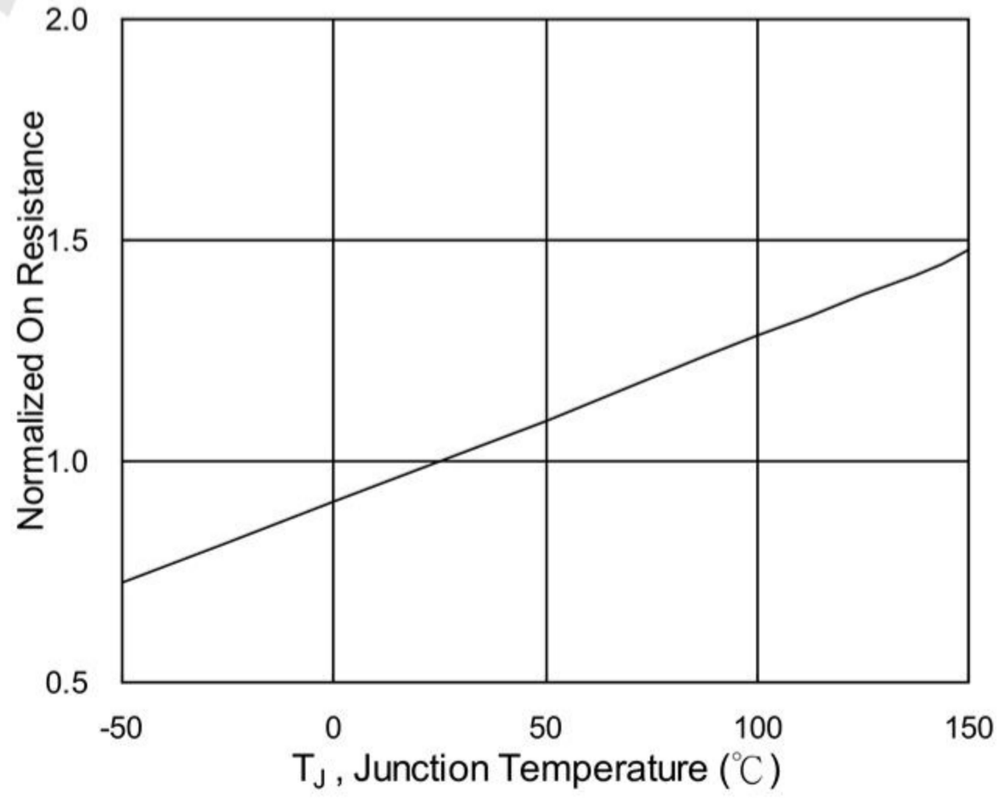


Fig.6 Normalized R_{DSON} vs. T_J

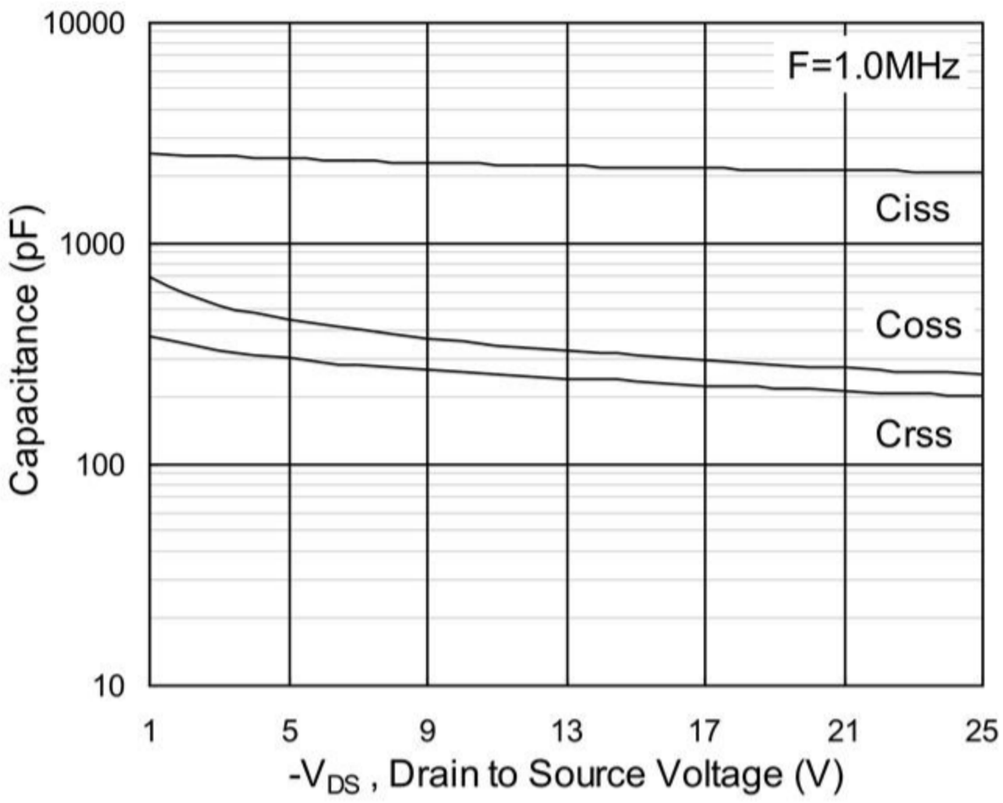


Fig.7 Capacitance

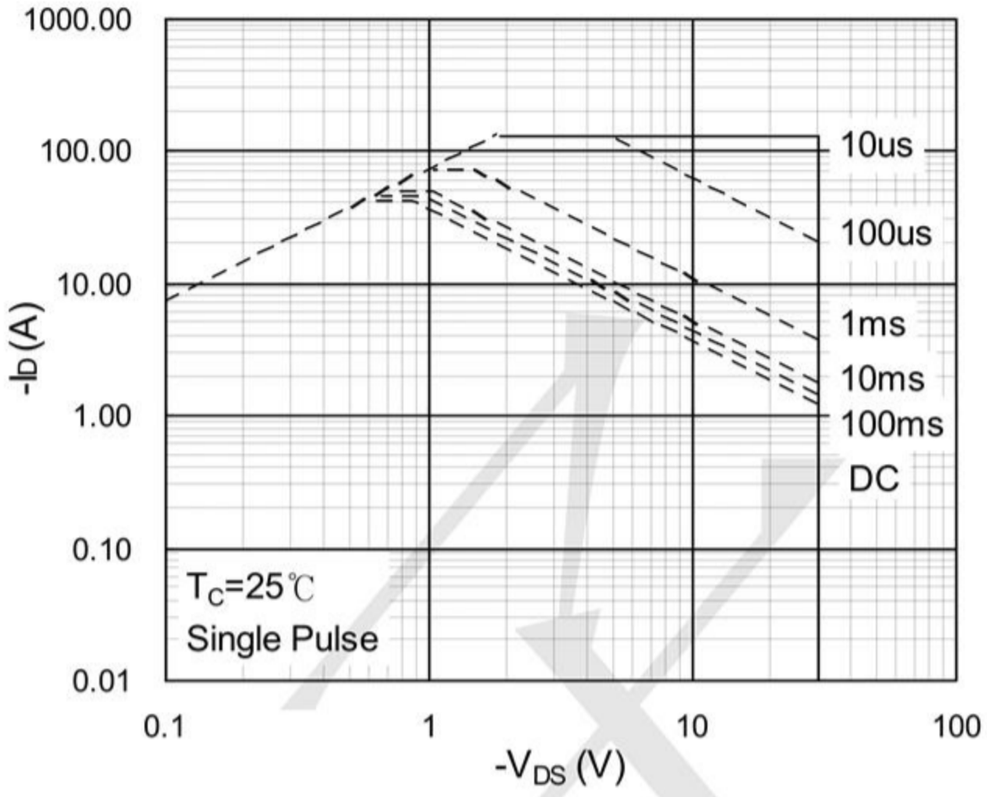


Fig.8 Safe Operating Area

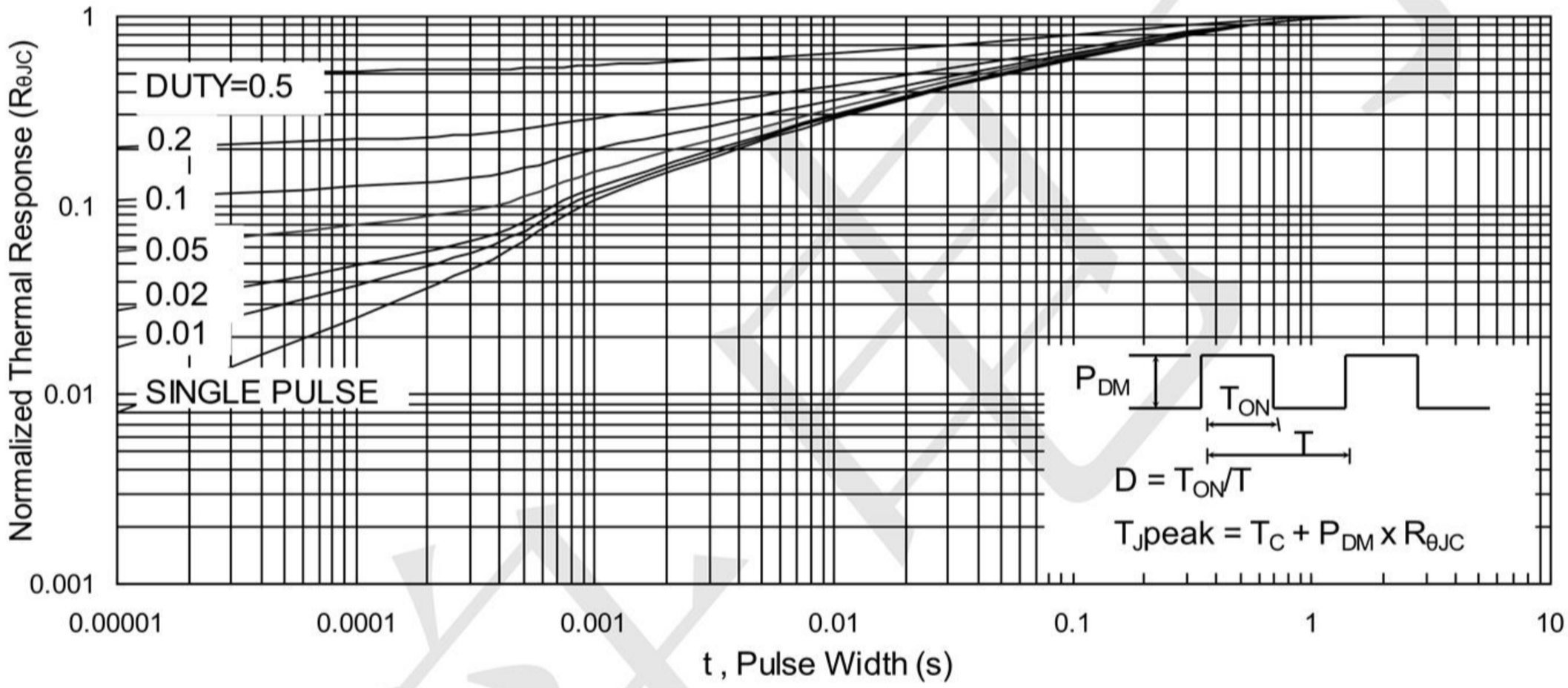


Fig.9 Normalized Maximum Transient Thermal Impedance

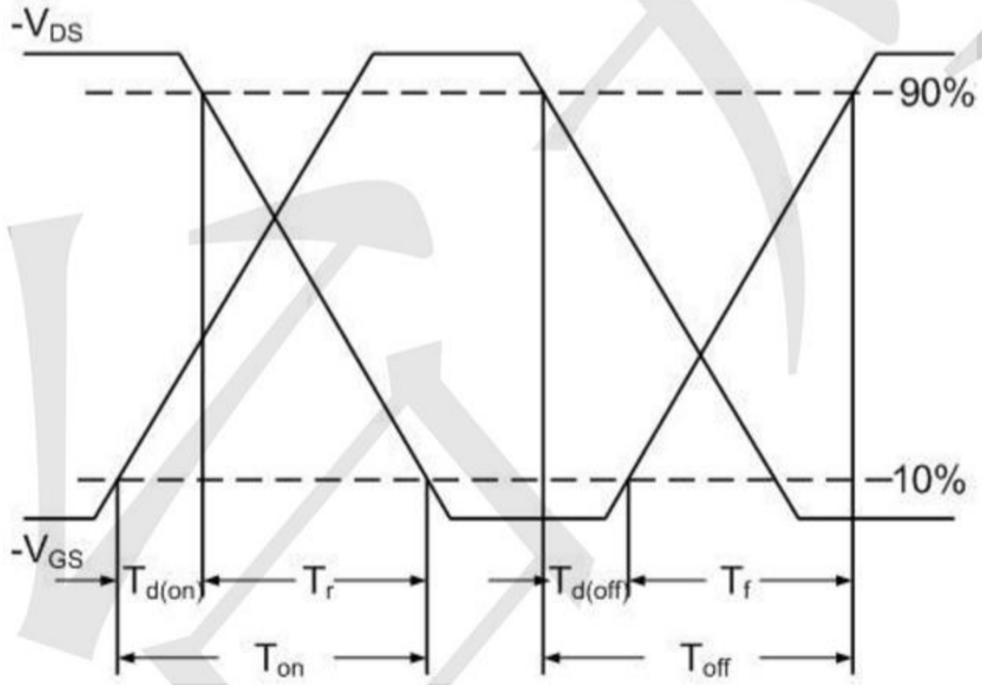


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times (-I_{AS}^2) \times \frac{-BV_{DSS}}{-BV_{DSS}-(-V_{DD})}$$

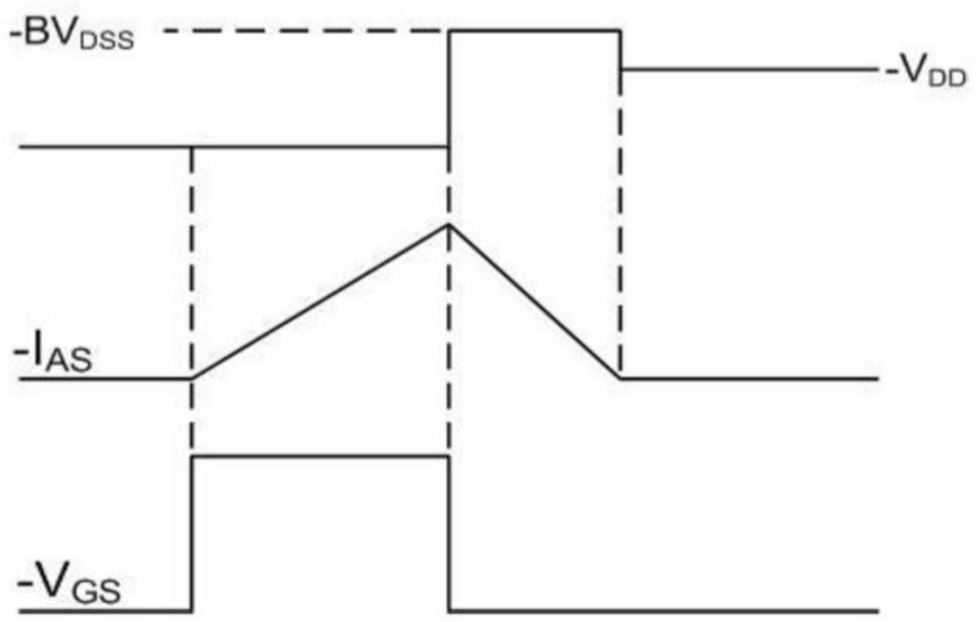
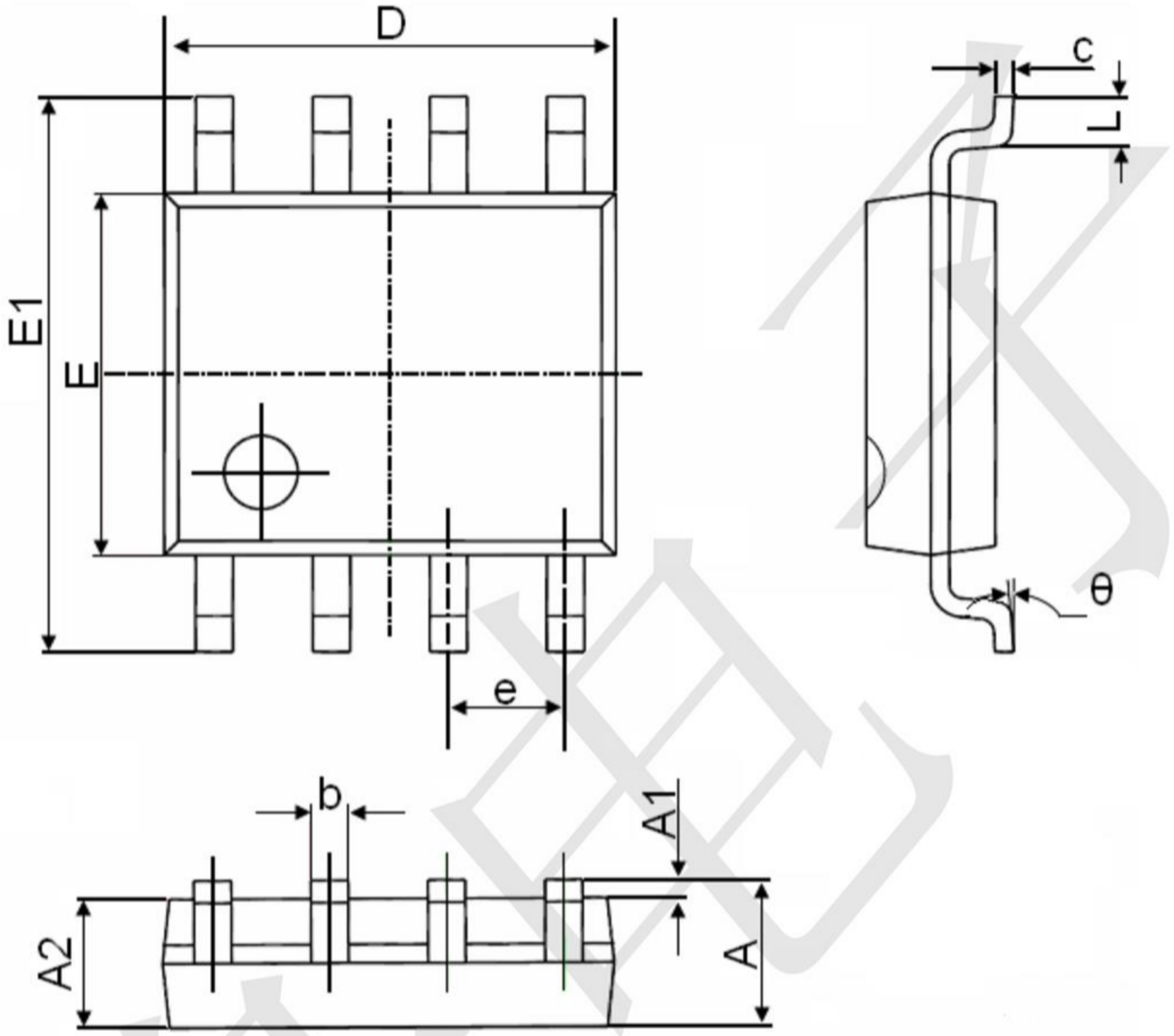


Fig.11 Unclamped Inductive Switching Waveform

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°